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AZOLES, METALS, AND SILICA SOLIDS IN WASTEWATER

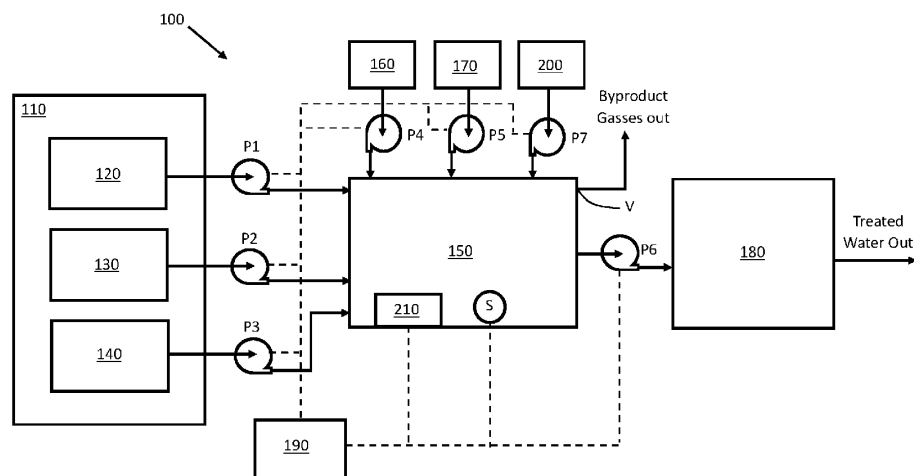


FIG. 1

(57) Abstract: A method for removing organic compounds from a copper-containing solution includes producing the copper-containing solution from a mixture of wastewater from a copper chemical mechanical polishing (CMP) operation of a semiconductor manufacturing facility and a concentrated copper waste stream (CCW) from the semiconductor manufacturing facility, and introducing an oxidizer into the copper-containing solution, the copper catalyzing production of hydroxyl radicals from the oxidizer that react with the organic compounds.

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